

(c) Remarks

The claims are 1-12 and 14 with claims 1-4 being independent. Claims 1-4 were amended to provide that the first and second steps form first and second layers of the deposited form wherein the the first and second layers are each identical semiconductor layers of the same conductivity type. See page 9, lines 20-24. The claims were also amended to recite the substrate is subject to a temperature rise above a pre-set temperature. Reconsideration of the claims is expressly requested.

Claims 1-12 and 14 were rejected as obvious over Moslehi '609 in view of Chan '811. The grounds of rejection are respectfully traversed.

In the final rejection of June 16, 2008 the Examiner noted the claims did not recite the same layer is formed of first and second sub layers and that the claims did not recite the problem solved. Accordingly, the claims have been amended to recite those features.

Prior to addressing the previously advanced grounds of rejection, Applicant wishes to briefly review again certain key features and advantages of the present claimed invention. In order to meet the problem of fluctuating temperatures during deposition and others, a plurality of discharge means are disposed in the reactor in order to provide better control of film formation temperature. When the substrate is conveyed through the reactor during film formation, power from RF power sources is applied to plural electrodes and is controlled or changed in order to form a deposited film of semiconductive layers having the same conductivity type. This is explicitly recited. The deposited film formed at the second stage is at a different position on the beltlike substrate from the corresponding film formed at the first stage. As noted in the Examples, the deposited films provide members with enhanced photoelectric conversion efficiency.

As noted pages 13 and 14 environmental temperature, including substrate temperature, rises during conventional film deposition. The substrate temperature rises over time to above the desired temperature maximum. Therefore, the present invention provides that discharge means is switched when the detected substrate temperature reaches a pre-set temperature. This feature is explicitly recited.

As shown in Figures 6 and 7 where the switching steps were not conducted then, for the comparative tests run, the initial photoelectric conversion efficiency decreased with the passage of time. On the other hand in the inventive Example 1, initial photoelectric conversion efficiency was restored after switching and open-circuit voltage was similarly restored.

In Moslehi the discharge means are different in kind from each other, ranging from u.v. irradiation to microwave irradiation, thermal heating, RF power and ECR plasma. These sources do not act in concert as in applicant's first and second electrodes connected to RF power sources to form deposited films of semiconductor layers and acting at different positions in a belt-like substrate. Moslehi is devoid of disclosure relating to applicant's first and second steps of applying electric power at pre-set temperatures at different belt positions.

In Chen, different plasmas form different layers. In Chen there is no teaching of employing plural electrodes to form the same film layer.

It should be understood the present invention is a process requiring specific steps conducted in the indicated order and at the indicated switching time. Moslehi fails to teach or suggest applicant's sequence of steps controlled by present switching indicia. There is no teaching in Moslehi or Chen, either individually or in combination, of the claimed sequence of steps. Moslehi actually creates the very problem applicant has solved. Having failed to understand the problem, how can Moslehi suggest a solution to an unknown problem. *Ex parte Wisdom*, (POBA 1973) 184 USP2 822.

Accordingly, Applicant submits that none of the references, whether alone or combined, discloses or suggests the present claimed invention nor renders it unpatentable. Accordingly, it is respectfully requested that the claims be allowed and that the case be passed to issue.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,

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